PATENT Attorney Docket No.: MLB-066C2

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### IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICANT:

Griffith et al.

SERIAL NO.:

10/646,146

**GROUP NO.:** 

Not Yet Assigned

FILING DATE:

August 22, 2003

**EXAMINER:** 

Not Yet Assigned

TITLE:

METHODS AND APPARATUS FOR MANUFACTURING ELECTRONIC

AND ELECTROMECHANICAL ELEMENTS AND DEVICES BY THIN-FILM

**DEPOSITION AND IMAGING** 

# CERTIFICATE OF FIRST CLASS MAILING UNDER 37 C.F.R. 1.8

I hereby certify that this correspondence, and any document(s) referred to as enclosed herein, is/are being deposited with the United States Postal Service as first class mail, postage prepaid, in an envelope addressed to the Commissioner for Patents, P.O. Box 1450, Alexandria VA 22313-1450 on this 10th day of December, 2003.

Anna-Karin Kuliga

Commissioner for Patents P.O. Box 1450 Alexandria VA 22313-1450

Sir:

#### Submitted herewith are:

- 1. Transmittal Form (1 page);
- 2. Information Disclosure Statement (2 pages);
- 3. Form PTO-1449 (3 pages); and
- 4. References cited (A1-A6, B1 and C1-C39); and
- 5. Return receipt postcard.

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			Examiner N	ame		Not Yet Assigned			
	FORM		Attorney Docket No.			MLB-066C2			
			Patent No.			Not applicable			
			Issue Date			Not applicable			
		EN	CLOSURES (c	heck all that apply)					
☐ Fe	e Transmittal Form		Copy of Notic	e to File Missing cation (PTO-1553)		Notice of Appeal to Board of Patent Appeals and Interferences			
	☐ Check Attached☐ Copy of Fee Transmittal Form		Formal Drawin	,					
	Amendment/Response		Request For Continued Examination (RCE) Transmittal			] Status Inquiry			
	After Final				∣⊠	Return Receipt Postcard			
	☐ Affidavits/declaration(s) ☐ Letter to Official ☐ Draftsperson including Drawings		Power of Attor (Revocation of	orney of Prior Powers)		Certificate of First Class Mailing under 37 C.F.R. 1.8			
	[Total Sheets]		Terminal Disclaimer			Certificate of Facsimile Transmission under 37 C.F.R. 1.8			
	Petition for Extension of Time			aration and Power r Utility or Design tion		Additional Enclosure(s) (please identify below)			
$\boxtimes$	Information Disclosure Statement		Small Entity Statement						
3	Form PTO-1449 Copies of IDS		CD(s) for large	CD(s) for large table or computer program					
	Certified Copy of Priority Document(s)		Amendment After Allowance						
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CORR	ESPONDENCE ADDRESS			SIGNATURE BLOCK					
Direct a	High Stre 125 High Boston, M Tel. No.:	rwitz & Thet Tower	nibeault, LLP	Date: December <u>10</u> , Reg. No. 45,054 Tel. No.: (617) 248- Fax No.: (617) 248-	-737	Jamie H. Rose Attorney for the Applicant			



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ELECTRONIC AND ELECTROMECHANICAL ELEMENTS AND DEVICES BY THIN-FILM DEPOSITION AND IMAGING

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

### INFORMATION DISCLOSURE STATEMENT

Sir:

In accordance with the provisions of 37 C.F.R. 1.97 and 1.98, Applicants hereby make of record the patents and publications listed on the accompanying Form PTO-1449, and other information contained herein, for consideration by the Examiner in connection with the examination of the above-identified patent application. Copies of the patents and publications are enclosed.

# **REMARKS**

In accordance with the provisions of 37 C.F.R. 1.97, this statement is being filed (CHECK ONE):

(1)	within three (3) months of the <b>filing date</b> of a national application other than a continued prosecution application under 37 C.F.R. 1.53(d), or within three (3) months of the <b>date of entry of the national stage</b> as set forth in 37 C.F.R. 1.491 in an international application, or before the mailing of the <b>first Office action</b> on the merits, or before the mailing of a <b>first Office action</b> after the filing of a request for continued examination under 37 C.F.R. 1.114; or
(2)	after the period defined in (1) but before the mailing date of a final action or a notice of allowance under 37 C.F.R. 1.311, and
	the requisite Statement is below, <b>OR</b>
	the requisite fee under 37 C.F.R. 1.17(p), namely \$180.00, is included herein, or

	(3		after the mailing date of a final action or notice of allowance but before the payment of the issue fee, AND
		] 1	the requisite Statement is below, AND
		] 1	the requisite petition fee under 37 C.F.R. 1.17(p), namely \$180.00 is included herein.
	_		Ily requested that each of the patents and publications listed on the attached Form
P10-	1449, an	ia oin	er information contained herein, be made of record in this application.
			STATEMENT
	As requi	red u	nder 37 C.F.R. 1.97(e), Applicant(s), through the undersigned, hereby state either that
_	_		riate space only if either (2) or (3) is checked on the previous page <u>and</u> the
State	ment is	requi	red]:
		1.	Each item of information contained in the Information Disclosure Statement was
			first cited in any communication from a foreign patent office in a counterpart
			foreign application not more than three months prior to the filing of the
			Information Disclosure Statement; or
		2.	No item of information contained in the Information Disclosure Statement was
			cited in a communication from a foreign patent office in a counterpart foreign
			application, and, to the knowledge of the person signing this Statement after
			making reasonable inquiry, no item of information contained in the Information
			Disclosure Statement was known to any individual designated in 37 C.F.R.
			1.56(c) more than three months prior to the filing of the Information
			Disclosure Statement.
			Respectfully submitted,
Doto	Decemb	.o. 10	2003
Date:	Decemi	JEI IU	, 2003

Tel. No.: (617) 248-7376 Fax No.: (617) 248-7100

Reg. No. 45,054

Attorney for Applicants
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High Street Tower 125 High Street

Jamie H. Rose

Boston, Massachusetts 02110

FORM PTO - 14 TRADESTINE INFORMATION DISCLOSURE STATEMENT

ATTORNEY DOCKET NO.: MLB-066C2

APPLICANT(S): Griffith et al.

SERIAL NO.: 10/646,146

FILING DATE: August 22, 2003 GROUP: Not Yet Assigned

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			U.S.	PATENT I	OCUMI	ENTS				
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	NAME			SUB CLASS	FILING DATE IF APPROPRIATE	
	Al	4,298,448	11/03/81	Muller et a	Muller et al.					
	A2	5,066,559	11/19/91	Elmasry et	al.					
	A3	5,380,362	01/10/95	Schubert	Schubert					
	A4	5,559,057	09/24/96	Goldstein						
·	A5	5,587,111	12/24/96	Watanabe	Watanabe et al.					
	A6	5,751,018	05/12/98	Alivisatos	et al.					
			FOREI	GN PATEN	T DOCU	MENTS				
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V	Bl	WO 97/38810	10/23/97	PCT				N		Y
		(	OTHER AF	RT, JOURN	AL ARTI	CLES, E	TC.			'
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)									
8	C1	Guo et al., "A Room-Temperature Silicon Single-Electron Metal-Oxide-Semiconductor Memory With Nanoscale Floating-Gate and Ultranarrow Channel," Appl. Phys. Lett. 70 (7), pp. 850-852, February 17, 1997.								
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1	C3 Guo et al., "Fabrication and Characterization of Room Temperature Silicon Single Electron Memory," J. Vac. Sci. Technol. B 15 (6), pp. 2840-2843, Nov./Dec. 1997.									
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1	C8 Tiwari et al., "Technology and Power-Speed Trade-Offs in Quantum-Dot and Nano-Crystal Memory Devices," Symposium on VLSI Technology Digest of Technical Papers, pp. 133-134, 1997.									

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ATTORNEY DOCKET NO.: MLB-066C2

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V	C10	Zollinger, Color Chemistry, 2 <sup>nd</sup> Ed.,	Weinheim, New York, pp. 352-361, 1991.		
i	C11	Murray et al., "Self-Organization of C Superlattices," Science, Vol. 270, pp	CdSe Nanocrystallites Into Three-Dimensional Quantum Dot . 1335-1338, November 24, 1995.		
υ	C12	Terris et al., "Near-Field Optical Data No. 4, pp. 388-390, July 25, 1994.	a Storage Using a Solid Immersion Lens," Appl. Phys. Lett., Vol. 65,		
V	C13	Markovich et al., "Parallel Fabrication and Single-Electron Charging of Devices Based on Ordered, Two-Dimensional Phases of Organically Functionalized Metal Nanocrystals," Appl. Phys. Lett. 70 (23), pp. 3170-3109, June 9, 1997.			
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V	C17	Tayaoka et al., "Preparation of Co-Fe-P Amorphous Fine Needles With Anodization Technique and Measurement of Demagnetizing Factor," J. Appl. Phys. 79 (8), pp. 6016-6018, April 15, 1996.			
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i	C20	Mamin et al., "High-Density Data Storage Using Proximal Probe Techniques," IBM J. Res. Develop., Vol. 39, No. 6, pp. 681-699, November 6, 1995.			
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V	C22	Terris et al., "Data Storage in NOS: Lifetime and Carrier-to-Noise Measurements," IEEE Transactions on Electron Devices, Vol. 42, No. 5, pp. 944-949, May 5, 1995.			
U	C23	Snow et al., "A Metal/Oxide Tunneling Transistor," Appl. Phys. Lett., 72 (23), pp. 3071-3073, June 8, 1998.			
J	C24	Minne et al., "Automated Parallel Hi 2340-2342, May 4, 1998.	gh-Speed Atomic Force Microscopy," Appl. Phys. Lett., 72 (18), pp.		
1	C25	Celotta et al., "Nanostructure Fabrication Via Laser-Focused Atomic Deposition (Invited)," J. Appl. Phys. 79 (8), pp. 6079-6083, April 15, 1996.			
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		N DISCLOSURE	APPLICANT(S): Griffith et al.  SERIAL NO.: 10/646,146				
STATEM	IEN I						
			FILI	ING DATE: August 22, 2003 GROUP: Not Yet Assigned			
V	C27	Doudin et al., "Arrays of Multilayere 15, 1996.	d Nan	owires (Invited)," J. Appl. Phys. 79 (8), pp. 60909-6094, April			
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V	C29	Bessho et al., "Fabricating Nanoscale Phys. 79 (8), pp. 5057-5059, April 13	-	netic Mounds Using a Scanning Probe Microscope," J. Appl. 6.			
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v	C37	Xia et al., "Soft Lithography," Angew. Chem. Int. Ed., Vol. 37, pp. 551-575, 1998.					
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EXAMINI	ER			DATE CONSIDERED			

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